

# Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

## **Quality Overview**

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
  - Class Q Military
  - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.



## 2N3905



## **PNP General Purpose Amplifier**

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 100 mA.

### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	200	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N3905	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

# PNP General Purpose Amplifier (continued)

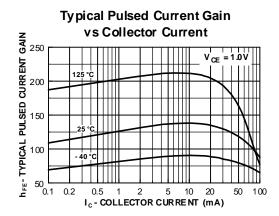
Symbol	Parameter	Test Conditions	Min	Max	Units
	DACTEDICTION				
	RACTERISTICS	1 40 50 4 1 0	40	ı	V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$			
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	40		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	5.0		V
CEX	Collector Cutoff Current	$V_{CE} = 30 \text{ V}, V_{OB} = 3.0 \text{ V}$		50	nA
BL	Base Cutoff Current	$V_{CE} = 30 \text{ V}, V_{OB} = 3.0 \text{ V}$		50	nA
ON CHAF	RACTERISTICS*				
ı <sub>FE</sub>	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 0.1 \text{ mA}$	30		
		$V_{CE} = 1.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	40		
		$V_{CE} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$	50	150	
		$V_{CE} = 1.0 \text{ V}, I_{C} = 50 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_{C} = 100 \text{ mA}$	30 15		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$	13	0.25	V
VCE(sat)	Concotor Emittor Cataration Voltage	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.40	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$	0.65	0.85	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage		0.65		
SMALL S	SIGNAL CHARACTERISTICS	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	0.65	0.85 0.95	V
SMALL S	SIGNAL CHARACTERISTICS Output Capacitance	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	0.65	0.85 0.95 4.5	V V
SMALL S	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance	$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$		0.85 0.95	V
SMALL S	SIGNAL CHARACTERISTICS Output Capacitance	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	2.0	0.85 0.95 4.5	V V
SMALL S Cob Cib	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance	$\begin{split} I_C &= 10 \text{ mA}, I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA}, I_B = 5.0 \text{ mA} \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V}, f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V}, f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA}, V_{CE} = 20 \text{ V}, \end{split}$		0.85 0.95 4.5	V V
SMALL S Cob Cib	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \end{split}$	2.0	0.85 0.95 4.5	pF pF
SMALL S	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ \end{split}$ $\begin{split} I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \end{split}$	2.0	0.85 0.95 4.5 10	PF PF
SMALL S Cob Cib Ofe Ore	Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ \end{split}$ $\begin{split} I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \end{split}$	2.0 50 0.1	0.85 0.95 4.5 10 200 5.0	V V PF PF x10 <sup>-4</sup> kΩ
	SIGNAL CHARACTERISTICS Output Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ \end{split}$ $\begin{split} I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \end{split}$	2.0 50 0.1 0.5	0.85 0.95 4.5 10 200 5.0 8.0	V V PF PF x10 <sup>-2</sup> kΩ
SMALL S Cob Cib Ofe Ofe Ofe	Output Capacitance Input Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ $\end{split}$ $V_{CE} &= 5.0 \text{ V, } I_C = 100  \mu\text{A, } \\ R_S &= 1.0  k\Omega, \end{split}$	2.0 50 0.1 0.5	0.85 0.95 4.5 10 200 5.0 8.0 40	V V V pF pF x10 <sup>-2</sup> kΩ μmho
SMALL S Cob Cib Ofe Ofe Ore	Output Capacitance Input Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ $\end{split}$ $V_{CE} = 5.0 \text{ V, } I_C = 100  \mu\text{A, } \end{split}$	2.0 50 0.1 0.5	0.85 0.95 4.5 10 200 5.0 8.0 40	V V V pF pF x10 <sup>-4</sup> kΩ μmho
SMALL S Cob Cib Ofe Ofe One No	Output Capacitance Input Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance Noise Figure	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ $\end{split}$ $V_{CE} &= 5.0 \text{ V, } I_C = 100  \mu\text{A, } \\ R_S &= 1.0  k\Omega, \end{split}$	2.0 50 0.1 0.5	0.85 0.95 4.5 10 200 5.0 8.0 40	V V V pF pF x10 <sup>-4</sup> kΩ μmho
SMALL S Cob Cib Ofe Ofe One No	Output Capacitance Input Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ $\end{split}$ $V_{CE} &= 5.0 \text{ V, } I_C = 100  \mu\text{A, } \\ R_S &= 1.0  k\Omega, \end{split}$	2.0 50 0.1 0.5	0.85 0.95 4.5 10 200 5.0 8.0 40	V V V pF pF x10 <sup>-4</sup> kΩ μmho:
SMALL S Cob Cib Ofe Ofe Noe NF	Output Capacitance Input Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance Noise Figure	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ $\end{split}$ $V_{CE} &= 5.0 \text{ V, } I_C = 100  \mu\text{A, } \\ R_S &= 1.0  k\Omega, \end{split}$	2.0 50 0.1 0.5	0.85 0.95 4.5 10 200 5.0 8.0 40	V V V pF pF x10 <sup>-4</sup> kΩ μmho:
SMALL S Cob Cib Ofe Ofe Noe NF	Output Capacitance Input Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance Noise Figure  NG CHARACTERISTICS	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ $V_{CE} &= 5.0 \text{ V, } I_C = 100  \mu\text{A, } \\ R_S &= 1.0 \text{ k}\Omega, \\ R_W &= 10 \text{ Hz to } 15.7 \text{ KHz} \\ \end{split}$	2.0 50 0.1 0.5	0.85 0.95 4.5 10 200 5.0 8.0 40 5.0	PF pF x10 <sup>-4</sup> kΩ μmho:
SMALL S Cob Cib Ofe Ofe One No	Output Capacitance Input Capacitance Input Capacitance Small-Signal Current Gain Small-Signal Current Gain Voltage Feedback Ratio Input Impedance Output Impedance Noise Figure  NG CHARACTERISTICS Delay Time	$\begin{split} I_C &= 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ I_C &= 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ \end{split}$ $\begin{split} V_{CB} &= 5.0 \text{ V, } f = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V, } f = 1.0 \text{ MHz} \\ I_C &= 10 \text{ mA, } V_{CE} = 20 \text{ V, } \\ f &= 100 \text{ MHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V, } \\ f &= 1.0 \text{ KHz} \\ \end{split}$ $\end{split}$ $\begin{split} V_{CE} &= 5.0 \text{ V, } I_C = 100  \mu\text{A, } \\ R_S &= 1.0  k\Omega, \\ B_W &= 10 \text{ Hz to } 15.7 \text{ KHz} \end{split}$	2.0 50 0.1 0.5	0.85 0.95 4.5 10 200 5.0 8.0 40 5.0	PF pF x10 <sup>-4</sup> kΩ μmhos dB

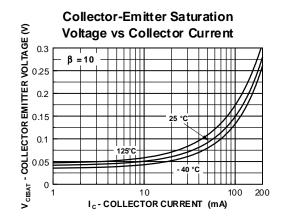
<sup>\*</sup>Pulse Test: Pulse Width  $\leq\!300\,\mu\text{s}$  , Duty Cycle  $\leq\!2.0\%$ 

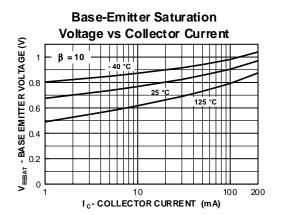
## **PNP General Purpose Amplifier**

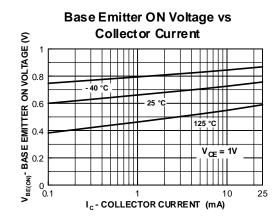
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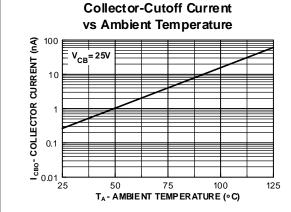
## **Typical Characteristics**

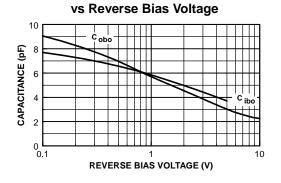












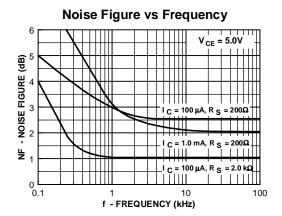
**Common-Base Open Circuit** 

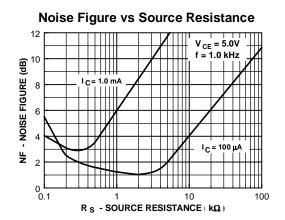
**Input and Output Capacitance** 

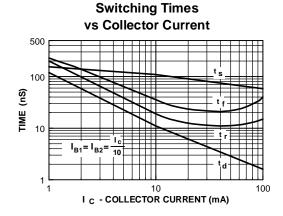
## **PNP General Purpose Amplifier**

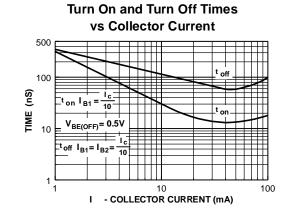
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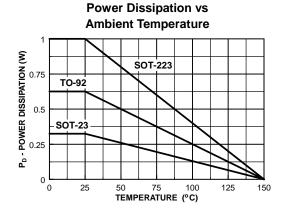
## Typical Characteristics (continued)







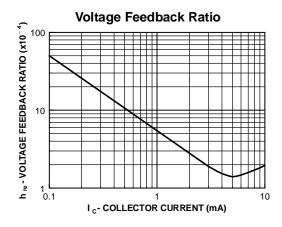


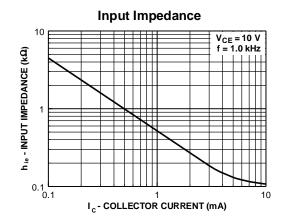


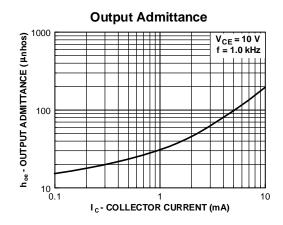
## **PNP General Purpose Amplifier**

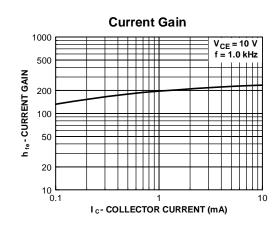
(continued)

## Typical Characteristics (continued)







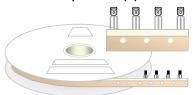


#### **TO-92 Tape and Reel Data** FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: Label 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

## TO-92 Tape and Reel Data, continued

# **TO-92 Reeling Style Configuration:** Figure 2.0

#### Machine Option "A" (H)

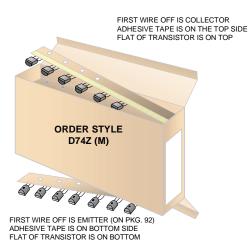


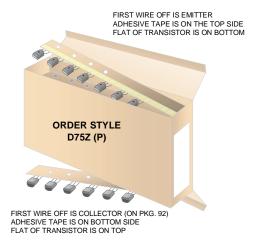
Style "A", D26Z, D70Z (s/h)

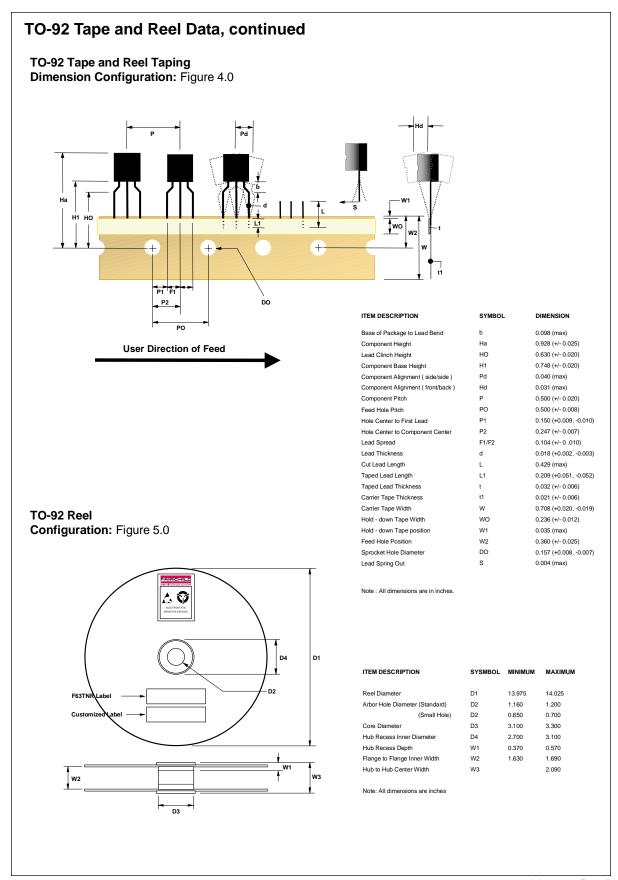
# Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

# **TO-92 Radial Ammo Packaging Configuration:** Figure 3.0



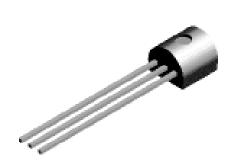


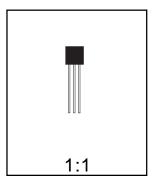


## **TO-92 Package Dimensions**



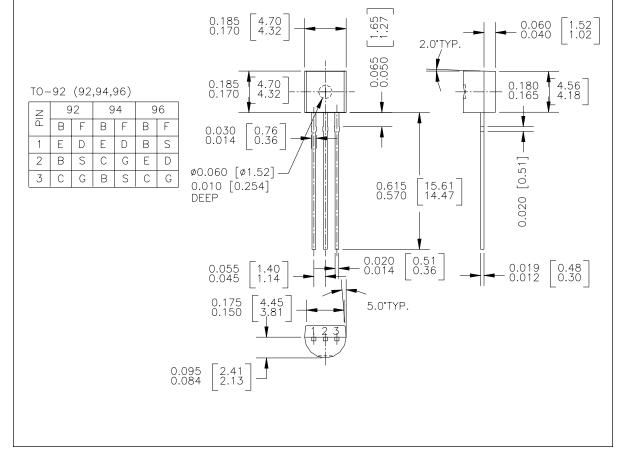
# TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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 $ACEx^{TM}$ FASTr™ PowerTrench® SyncFET™ Bottomless™ QFET™ TinyLogic™ GlobalOptoisolator™ QSTM UHC™ CoolFET™ GTO™ **VCX**<sup>TM</sup>  $CROSSVOLT^{TM}$ QT Optoelectronics™ HiSeC™

DOME™ ISOPLANAR™ Quiet Series™

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#### LIFE SUPPORT POLICY

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- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.